

NSCT817-25LT1G, NSCT817-40LT1G

General Purpose Transistors

NPN Silicon

Features

- These are Pb-Free Devices

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	45	V
Collector – Base Voltage	V_{CBO}	50	V
Emitter – Base Voltage	V_{EBO}	5.0	V
Collector Current – Continuous	I_C	500	mA _{dc}

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

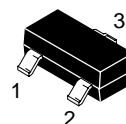
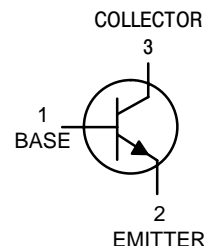
1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.



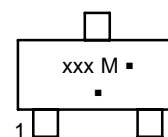
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**SOT-23
CASE 318
STYLE 6**

MARKING DIAGRAM



xxx = Specific Device Code
(725 for -25 device)
(74L for -40 device)
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NSCT817-25LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
NSCT817-40LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
NSCT817-25LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel
NSCT817-40LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$)	$V_{(BR)CEO}$	45	–	–	V
Collector–Emitter Breakdown Voltage ($V_{EB} = 0$, $I_C = -10\text{ }\mu\text{A}$)	$V_{(BR)CES}$	50	–	–	V
Emitter–Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$)	$V_{(BR)EBO}$	5.0	–	–	V
Collector Cutoff Current ($V_{CB} = 20\text{ V}$) ($V_{CB} = 20\text{ V}$, $T_A = 150^\circ\text{C}$)	I_{CBO}	– –	– –	100 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ V}$) ($I_C = 500\text{ mA}$, $V_{CE} = 1.0\text{ V}$)	h_{FE}	160 250 40	– – –	400 600 –	–
Collector–Emitter Saturation Voltage ($I_C = 500\text{ mA}$, $I_B = 50\text{ mA}$)	$V_{CE(sat)}$	–	–	0.7	V
Base–Emitter On Voltage ($I_C = 500\text{ mA}$, $V_{CE} = 1.0\text{ V}$)	$V_{BE(on)}$	–	–	1.2	V
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	–	–	MHz
Output Capacitance ($V_{CB} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	–	10	–	pF

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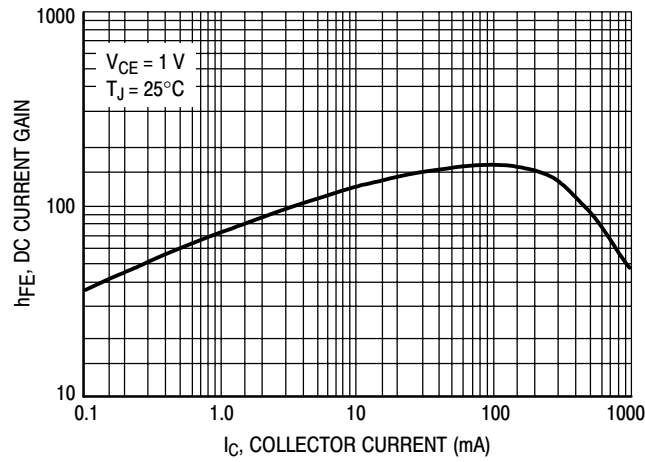


Figure 1. DC Current Gain

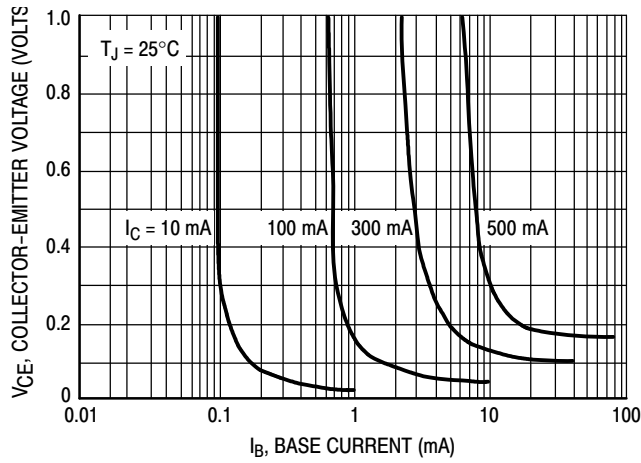


Figure 2. Saturation Region

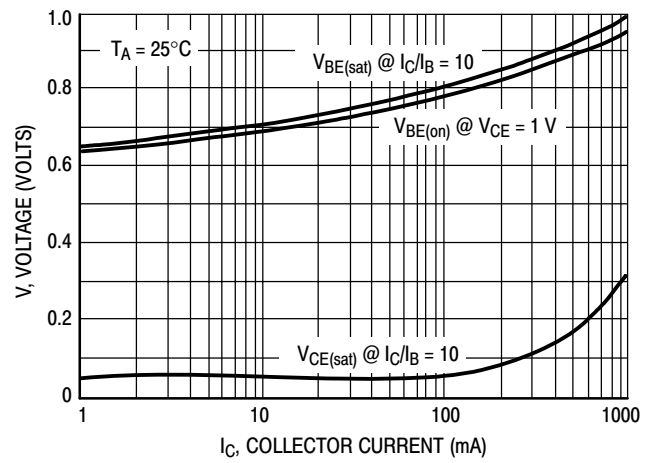


Figure 3. "On" Voltages

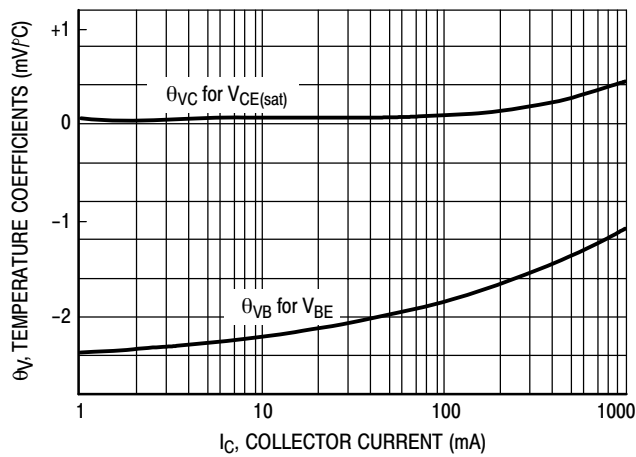


Figure 4. Temperature Coefficients

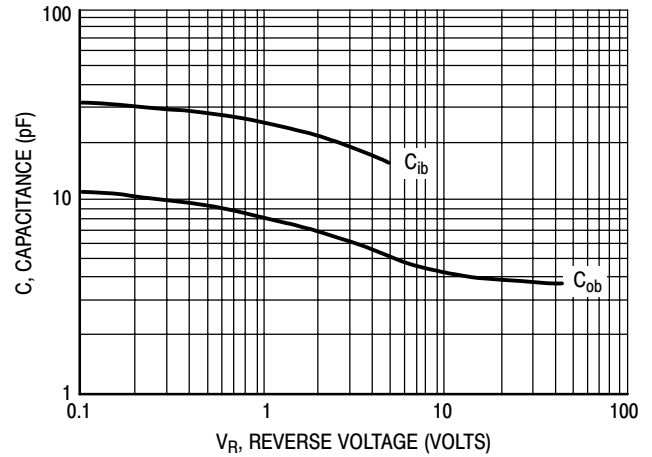


Figure 5. Capacitances

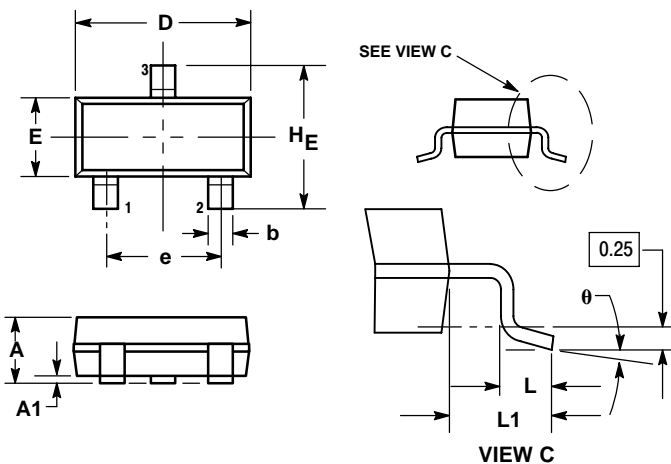
NSCT817-25LT1G, NSCT817-40LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)

CASE 318-08

ISSUE AN



NOTES:

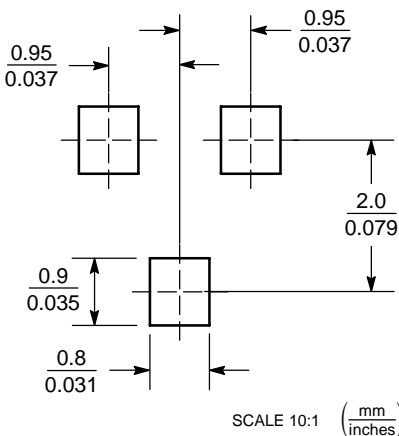
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104


STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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